

Enhancing Photoresponsivity of Self-Aligned MoS₂ Field-Effect Transistor by Piezo-Phototronic Effect from GaN Nanowire

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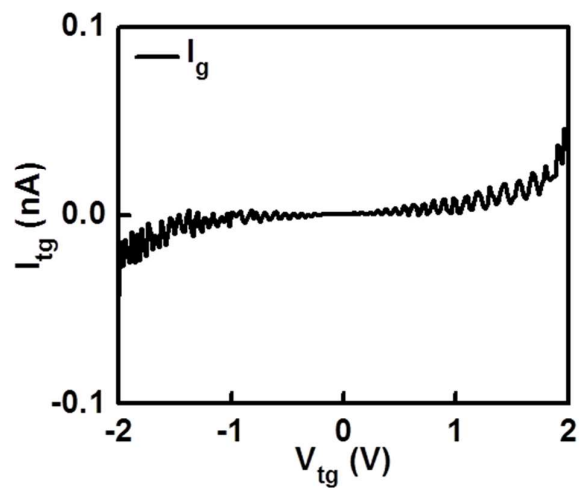


Figure S1. The gate leakage current of the self-aligned MoS₂ FET.

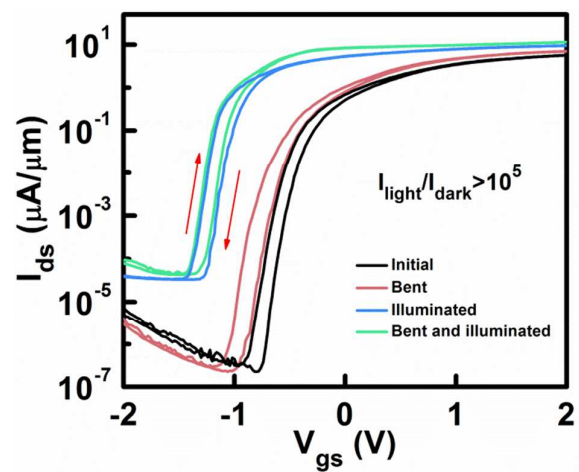


Figure S2. Comparison of the transfer characteristics of the same device under different test conditions with the arrows indicating hysteresis direction.